## SQ3426EEV

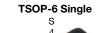


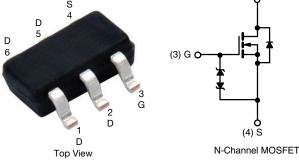
**Vishay Siliconix** 

# Automotive N-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	60		
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS}$ = 10 V	0.042		
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS}$ = 4.5 V	0.063		
I <sub>D</sub> (A)	7		
Configuration	Single		

(1, 2, 5, 6) D





#### FEATURES

- TrenchFET<sup>®</sup> power MOSFET
- Typical ESD protection 800 V HBM
- AEC-Q101 qualified
- 100 % R<sub>g</sub> and UIS tested
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>



RoHS COMPLIANT HALOGEN FREE

Marking	Code <sup>.</sup>	84777
warking	Coue.	οπλλλ

ORDERING INFORMATION		
	Package	TSOP-6
	Lead (Pb)-free and Halogen-free	SQ3426EEV-T1-GE3

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C, unless otherwise noted)						
PARAMETER		SYMBOL	LIMIT	UNIT		
Drain-Source Voltage	Drain-Source Voltage		60	V		
Gate-Source Voltage		V <sub>GS</sub>	± 20	v		
Continuous Drain Current	T <sub>C</sub> = 25 °C	- I <sub>D</sub>	7			
	T <sub>C</sub> = 125 °C		4			
Continuous Source Current (Diode Conduction)			6	А		
Pulsed Drain Current <sup>a</sup>			29			
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	10			
Single Pulse Avalanche Energy		E <sub>AS</sub>	5	mJ		
Maximum Power Dissipation <sup>a</sup>	T <sub>C</sub> = 25 °C	PD	5	W		
	T <sub>C</sub> = 125 °C		1.6	~~		
Operating Junction and Storage Temperature Ran	nge	T <sub>J</sub> , T <sub>stg</sub>	- 55 to +175	°C		

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount <sup>b</sup>	R <sub>thJA</sub>	110	°C/W
Junction-to-Foot (Drain)		R <sub>thJF</sub>	30	0/00

Notes

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

b. When mounted on 1" square PCB (FR-4 material).

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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static						<u> </u>		
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub>	= 0, I <sub>D</sub> = 250 μA	60	-	-		
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	= V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1.5	-	2.5	V	
Coto Course Leokers		$V_{DS} = 0 V, V_{GS} = \pm 12 V$		-	-	± 500	nA	
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	0 V, $V_{GS} = \pm 20 V$	-	-	± 1	mA	
		$V_{GS} = 0 V$	V <sub>DS</sub> = 60 V	-	-	1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 60 V, T <sub>J</sub> = 125 °C	-	-	50	μA	
		$V_{GS} = 0 V$	$V_{DS} = 60 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$	-	-	150		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 V$	10	-	-	Α	
		$V_{GS} = 10 V$	I <sub>D</sub> = 5 A	-	0.035	0.042		
Drain Source On State Desistance a	Р	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 5 A, T <sub>J</sub> = 125 °C	-	0.059	0.076	Ω	
Drain-Source On-State Resistance <sup>a</sup>	tance a $R_{DS(on)}$ $V_{GS} = 10 V$ $I_D = 5 A, T_J = 175 ^{\circ}C$ - $V_{GS} = 4.5 V$ $I_D = 4 A$ -	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 5 A, T <sub>J</sub> = 175 °C	-	0.074	0.095		
		0.057	0.063					
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub>	= 15 V, I <sub>D</sub> = 4 A	-	12	-	S	
Dynamic <sup>b</sup>	<u>.</u>					•	•	
Input Capacitance	C <sub>iss</sub>		' <sub>GS</sub> = 0 V V <sub>DS</sub> = 30 V, f = 1 MHz	-	560	700	pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$		-	85	105		
Reverse Transfer Capacitance	C <sub>rss</sub>	_		-	55	70		
Total Gate Charge <sup>c</sup>	Qg		$V_{DS} = 30 \text{ V}, \text{ I}_{D} = 4 \text{ A}$	-	7.6	12		
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{GS} = 4.5 V$		-	2.1	-	nC	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>	_		-	4.1	-		
Gate Resistance	Rg	f = 1 MHz		1.2	2.4	3.6	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	9	14		
Rise Time <sup>c</sup>	t <sub>r</sub>	V <sub>DD</sub> =	$V_{DD}$ = 30 V, R <sub>L</sub> = 7.5 Ω		12	18	- ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 4 \text{ A}, V_{GEN} = 10 \text{ V}, \text{ R}_g = 1 \Omega$		-	19	29		
Fall Time <sup>c</sup>	t <sub>f</sub>			-	7	11		
Source-Drain Diode Ratings and Charact	eristics <sup>b</sup>							
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	29	Α	
Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> =	-	0.75	1.2	V		

Notes

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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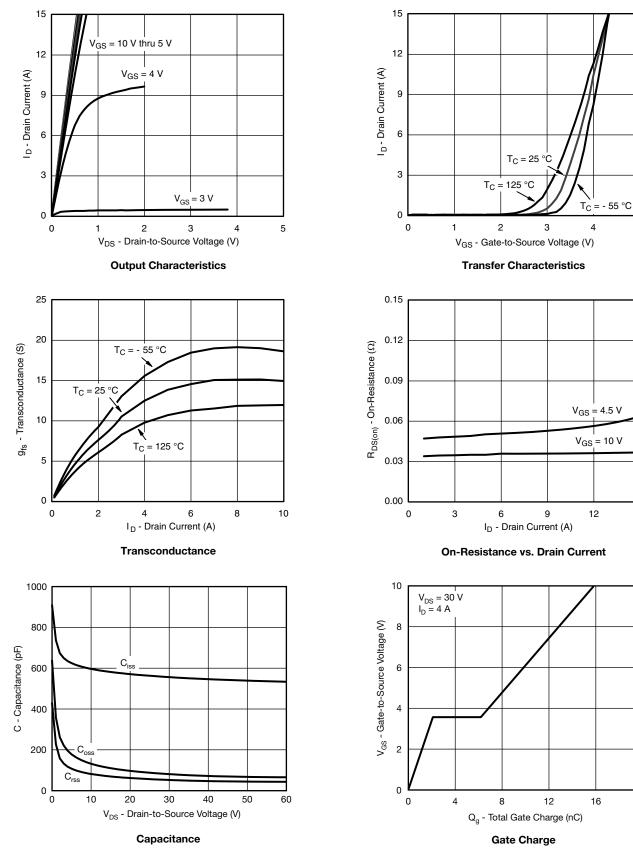
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### **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)

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For technical questions, contact: <u>automostechsupport@vishay.com</u>

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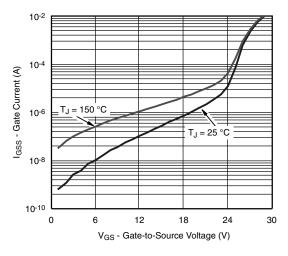




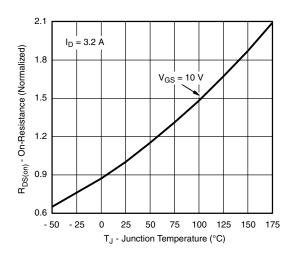
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**SQ3426EEV** 

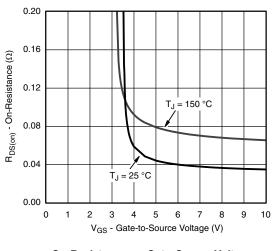
### TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



Gate Current vs. Gate-Source Voltage



**On-Resistance vs. Junction Temperature** 

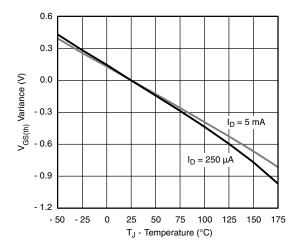


**On-Resistance vs. Gate-Source Voltage** 

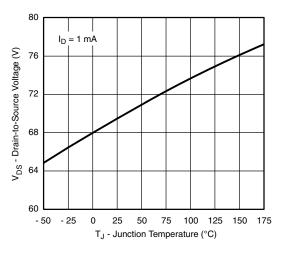
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100 10 T<sub>J</sub> = 150 °C Is - Source Current (A) 1 T<sub>.1</sub> = 25 °C 0.1 0.01 0.001 0.2 0.8 1.0 0.0 0.4 0.6 1.2 V<sub>SD</sub> - Source-to-Drain Voltage (V)

Source-Drain Diode Forward Voltage







Drain-Source Breakdown vs. Junction Temperature

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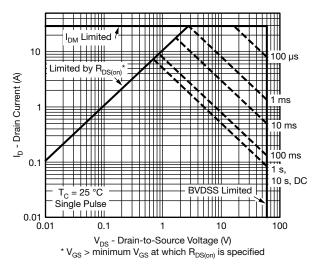
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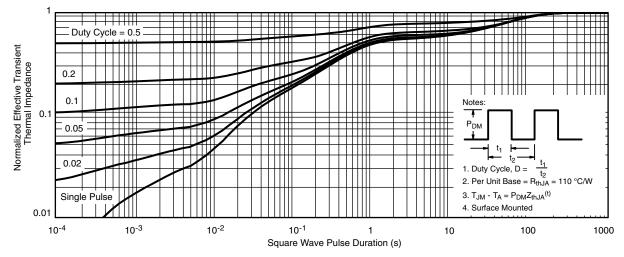
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#### **THERMAL RATINGS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



Safe Operating Area



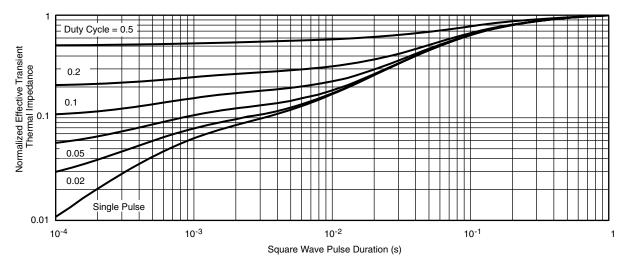
Normalized thermal Transient Impedance, Junction-to-Ambient





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#### **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized thermal Transient Impedance, Junction-to-Foot

#### Note

• The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction to Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction to Foot (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="http://www.vishay.com/ppg?65351">www.vishay.com/ppg?65351</a>.



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